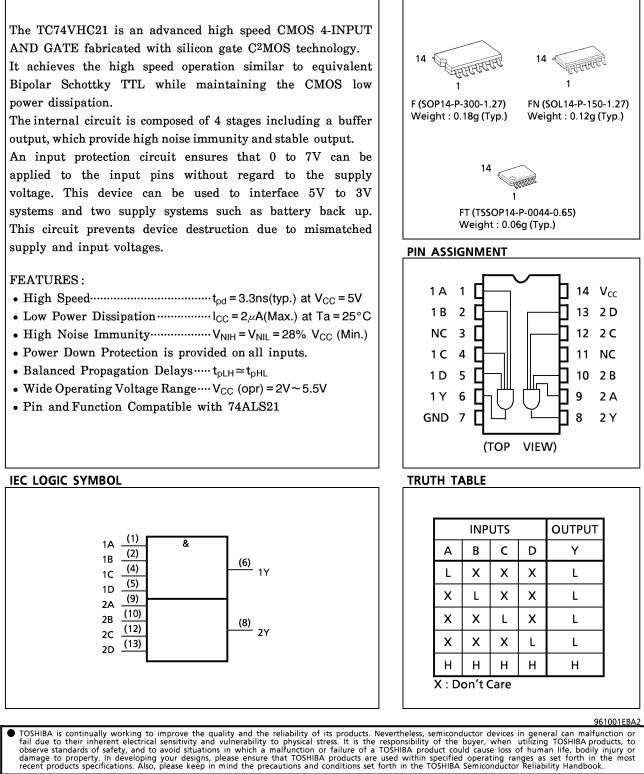
TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74VHC21F, TC74VHC21FN, TC74VHC21FT

### DUAL 4-INPUT AND GATE

(Note) The JEDEC SOP (FN) is not available in Japan.



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#### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V <sub>cc</sub>	-0.5~7.0	V
DC Input Voltage	VIN	-0.5~7.0	V
DC Output Voltage	V <sub>OUT</sub>	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	Ι <sub>ικ</sub>	- 20	mA
Output Diode Current	Ι <sub>οκ</sub>	±20	mA
DC Output Current	I <sub>OUT</sub>	±25	mA
DC V <sub>cc</sub> /Ground Current	I <sub>cc</sub>	± 50	mA
Power Dissipation	PD	180	mW
Storage Temperature	T <sub>stg</sub>	-65~150	°C

### **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V <sub>cc</sub>	2.0~5.5	V
Input Voltage	VIN	0~5.5	V
Output Voltage	V <sub>OUT</sub>	0~V <sub>cc</sub>	V
Operating Temperature	T <sub>opr</sub>	opr - 40~85	
Input Rise and Fall Time	dt/dv	0~100 (V <sub>CC</sub> = 3.3 ± 0.3V) 0~20 (V <sub>CC</sub> = 5±0.5V)	ns / V

#### DC ELECTRICAL CHARACTERISTICS

PARAMETER SYMBOL		TEST CONDITION		V <sub>cc</sub>	Ta = 25°C			Ta = 4	UNIT	
			(V)	MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	VIH			2.0 3.0~ 5.5	1.50 V <sub>cc</sub> × 0.7	-	-	1.50 V <sub>cc</sub> ×0.7		v
Low - Level Input Voltage	VIL			2.0 3.0~ 5.5	-	_	0.50 V <sub>cc</sub> ×0.3	_	0.50 V <sub>cc</sub> × 0.3	v
High - Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub>	I <sub>ОН</sub> = — 50µА	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		v
			I <sub>OH</sub> = — 4mA I <sub>OH</sub> = — 8mA	3.0 4.5	2.58 3.94	-	_	2.48 3.80		
Low - Level Output Voltage V <sub>OL</sub>	V <sub>1 N</sub> =	I <sub>OL</sub> = 50μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	v	
	V <sub>IH</sub> or V <sub>IL</sub>	$I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44		
Input Leakage Current	I <sub>IN</sub>	$V_{IN} = 5.5V \text{ or } GND$		0~5.5		_	±0.1	—	± 1.0	μA
Quiescent Supply Current	I <sub>cc</sub>	$V_{IN} = V_{CC} \text{ or } GND$		5.5	_	_	2.0	_	20.0	$\mu$ A

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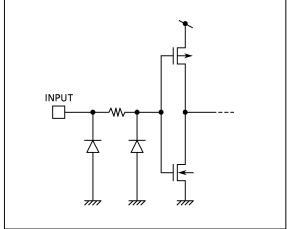
## AC ELECTRICAL CHARACTERISTICS ( Input $t_r = t_f = 3ns$ )

PARAMETER	SYMBOL	TES	TEST CONDITION		Ta = 25°C			Ta = −40~85°C		UNIT
	STIVIBUL		V <sub>cc</sub> (V)	CL (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time	t <sub>pLH</sub> t <sub>pHL</sub>		3.3±0.3	15	-	4.8	7.0	1.0	8.5	ns
				50	-	7.3	10.5	1.0	12.0	
			5.0 ± 0.5	15	-	3.3	5.0	1.0	6.0	
			$5.0 \pm 0.5$	50	-	4.8	7.0	1.0	8.0	
Input Capacitance	C <sub>IN</sub>				—	4	10	—	10	μE
Power Dissipation Capacitance	C <sub>PD</sub>	(	Note 1)		_	20	_	_	_	pF

Note (1)  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :  $I_{CC\,(opr.)}=C_{PD}\cdot V_{CC}\cdot f_{\,|N}+I_{CC}\,/\,2\,(\,per\,\,Gate\,)$ 

#### **INPUT EQUIVALENT CIRCUIT**



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